NSN 5961-01-080-1892

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-080-1892 **Inclosure Material:** Metal **Overall Length:** Between 0.240 inches and 0.260 inches **Terminal Length:** 1.500 inches **Overall Diameter:** Between 0.335 inches and 0.370 inches **Internal Configuration:** Junction contact **Mounting Method: Terminal Terminal Circle Diameter:** 0.200 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 6.0 gate voltage, dc **Current Rating Per Characteristic:** 3.00 milliamperes zero-gate-voltage source current torr **Power Rating Per Characteristic:** 0.1 milliwatts small-signal input power, common-collector peak **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Test Data Document:** 19200-11733685 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No